



ICAPS AND PACKAGING MASTER CLASS

September 8, 2021

Forward-Looking Statements and Other Information

Today's presentations contain forward-looking statements, including those regarding anticipated growth and trends in our businesses and markets, industry outlooks and demand drivers, technology transitions, our business and financial performance and market share positions, our capital allocation and cash deployment strategies, our investment and growth strategies, our development of new products and technologies, our business outlook for the fourth quarter of fiscal 2021 and beyond, the impact of the ongoing COVID-19 pandemic and responses thereto on our operations and financial results, and other statements that are not historical facts. These statements and their underlying assumptions are subject to risks and uncertainties and are not guarantees of future performance.

Factors that could cause actual results to differ materially from those expressed or implied by such statements include, without limitation: the level of demand for our products, our ability to meet customer demand, and our suppliers' ability to meet our demand requirements; global economic and industry conditions; the effects of regional or global health epidemics, including the severity and duration of the ongoing COVID-19 pandemic; global trade issues and changes in trade and export license policies, including rules and interpretations promulgated by U.S. Department of Commerce expanding export license requirements for certain products sold to certain entities in China; consumer demand for electronic products; the demand for semiconductors; customers' technology and capacity requirements; the introduction of new and innovative technologies, and the timing of technology transitions; our ability to develop, deliver and support new products and technologies; the concentrated nature of our customer base; acquisitions, investments and divestitures; changes in income tax laws; our ability to expand our current markets, increase market share and develop new markets; market acceptance of existing and newly developed products; our ability to obtain and protect intellectual property rights in key technologies; our ability to achieve the objectives of operational and strategic initiatives, align our resources and cost structure with business conditions, and attract, motivate and retain key employees; the variability of operating expenses and results among products and segments, and our ability to accurately forecast future results, market conditions, customer requirements and business needs; and other risks and uncertainties described in our SEC filings, including our recent Forms 10-Q and 8-K. All forward-looking statements are based on management's current estimates, projections and assumptions, and we assume no obligation to update them.

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2021 Master Classes

WELCOME

Michael Sullivan

Corporate Vice President

Head of Investor Relations

ICAPS and PACKAGING MASTER CLASS | September 8, 2021

UPCOMING INVESTOR EVENTS

MASTER CLASSES

April 6	May 5	June 16	September 8	October 18*
2021 Investor Meeting	Memory	Logic	ICAPS & Advanced Packaging	Process Control & AppliedPRO™

* Projected Date

AGENDA

- 9:00 **PART 1** HOST: Mike Sullivan
Foundry-Logic Growth Thesis
Fireside Chat | Tom Caulfield, Ph.D., GlobalFoundries
- 9:15 **PART 2** HOST: Sundar Ramamurthy, Ph.D.
ICAPS and Advanced Packaging Introduction
ICAPS | Michael Chudzik, Ph.D.
Packaging | Nirmalya Maity, Ph.D.
- 9:55 **PART 3** HOST: Sundar Ramamurthy, Ph.D.
ICAPS and Advanced Packaging Growth Opportunities
- 10:05 **Q&A** Sundar, Nirmalya, Mike

TAKEAWAY

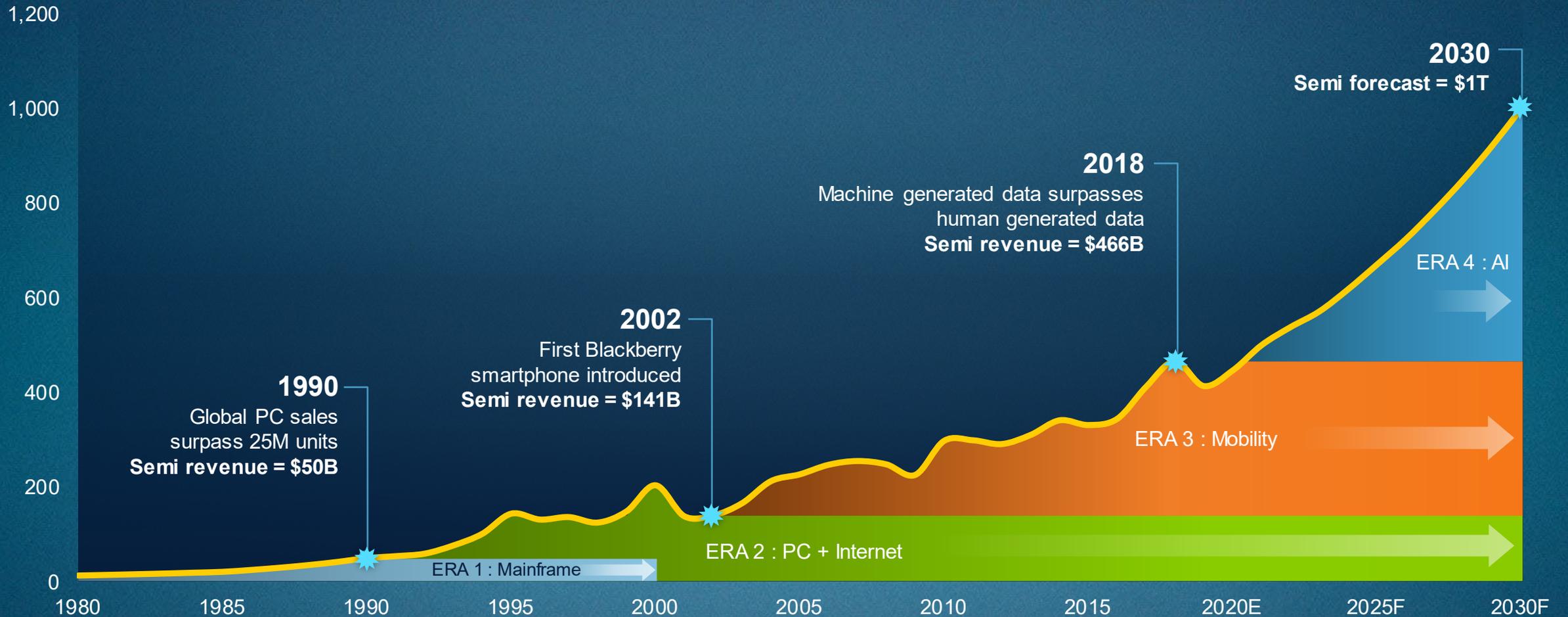
Messages

1. ICAPS markets fuel data generation at the edge and demand for leading-edge logic and memory in the cloud
2. Advanced packaging enables the PPACT™ benefits associated with Moore's Law to continue
3. Applied's unique portfolio breadth enables outperformance in ICAPS and advanced packaging

* Non-GAAP adjusted EPS

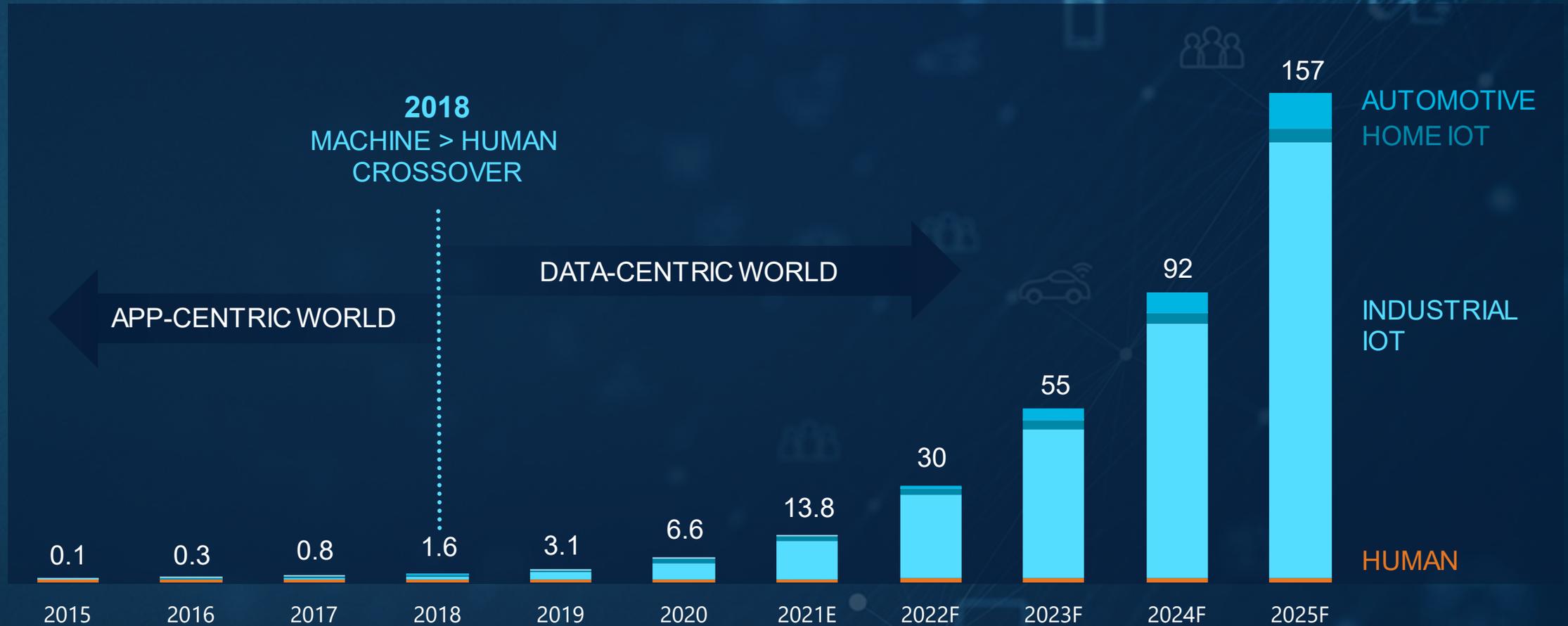
Applied Materials External Use

Semiconductor Industry Revenue (\$B)



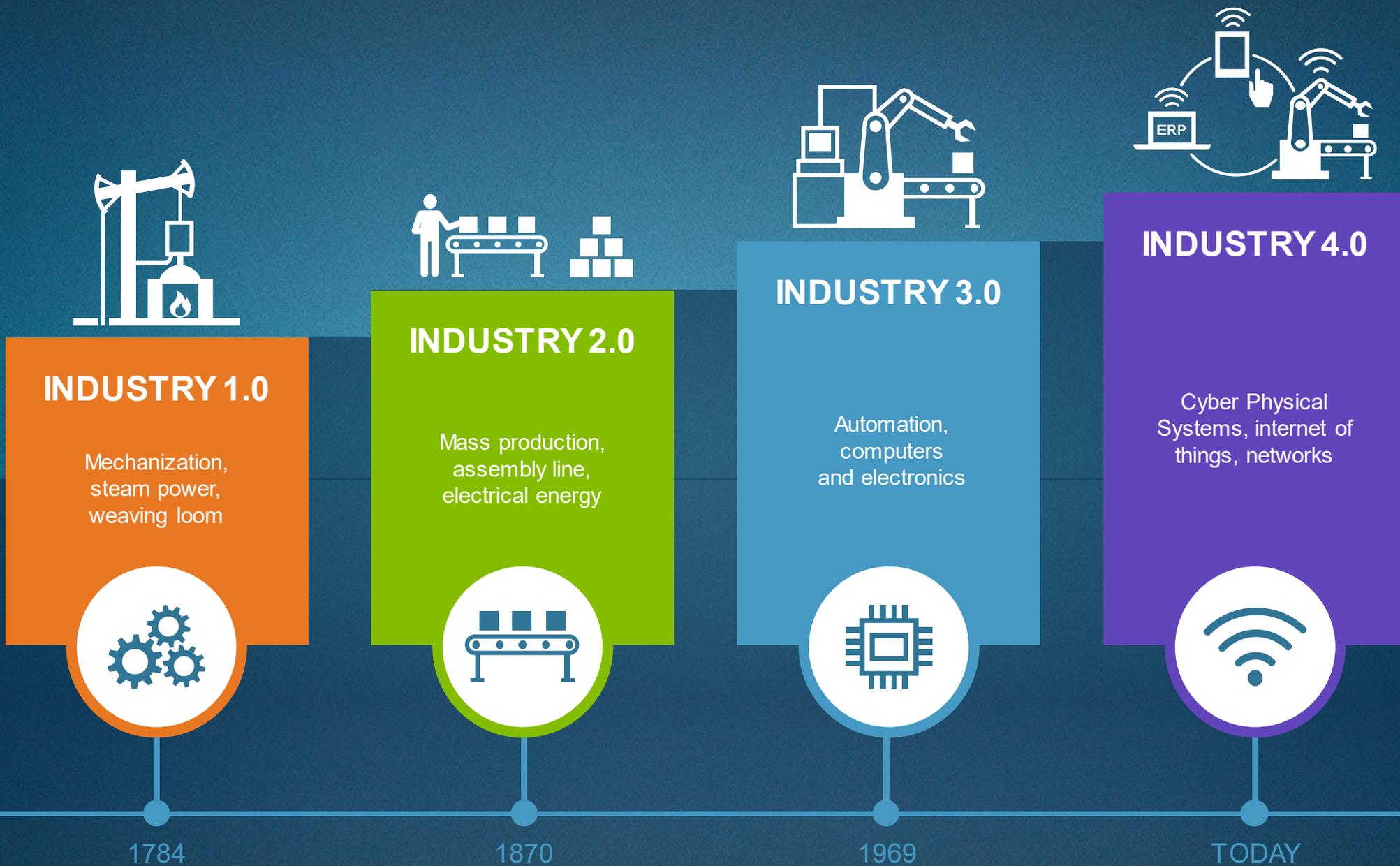
AI ERA WILL BE BIGGEST AGE OF COMPUTING

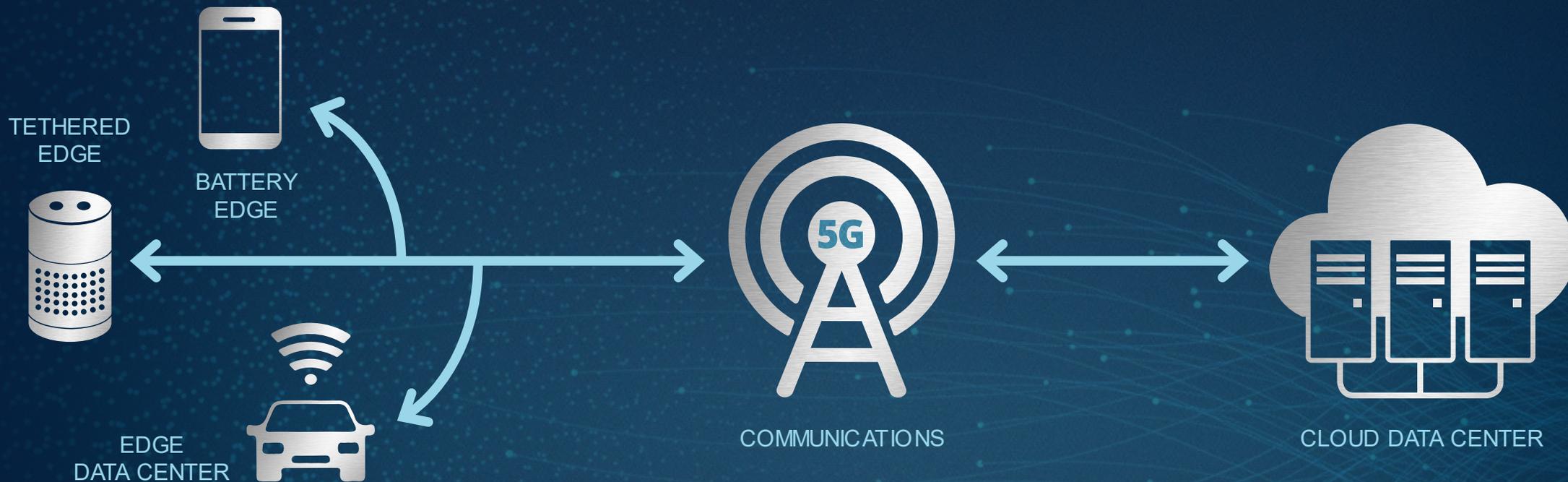
Data Generation By Category (ZB)



SEMI GROWTH NO LONGER LIMITED BY HUMAN CONSUMPTION

Source: Applied Materials





Explosion of
data generation

+

**Faster, higher-bandwidth
communications** to
move data around

+

AI computing to make
sense of all the data
and create value

AI = ACTIONABLE INSIGHT

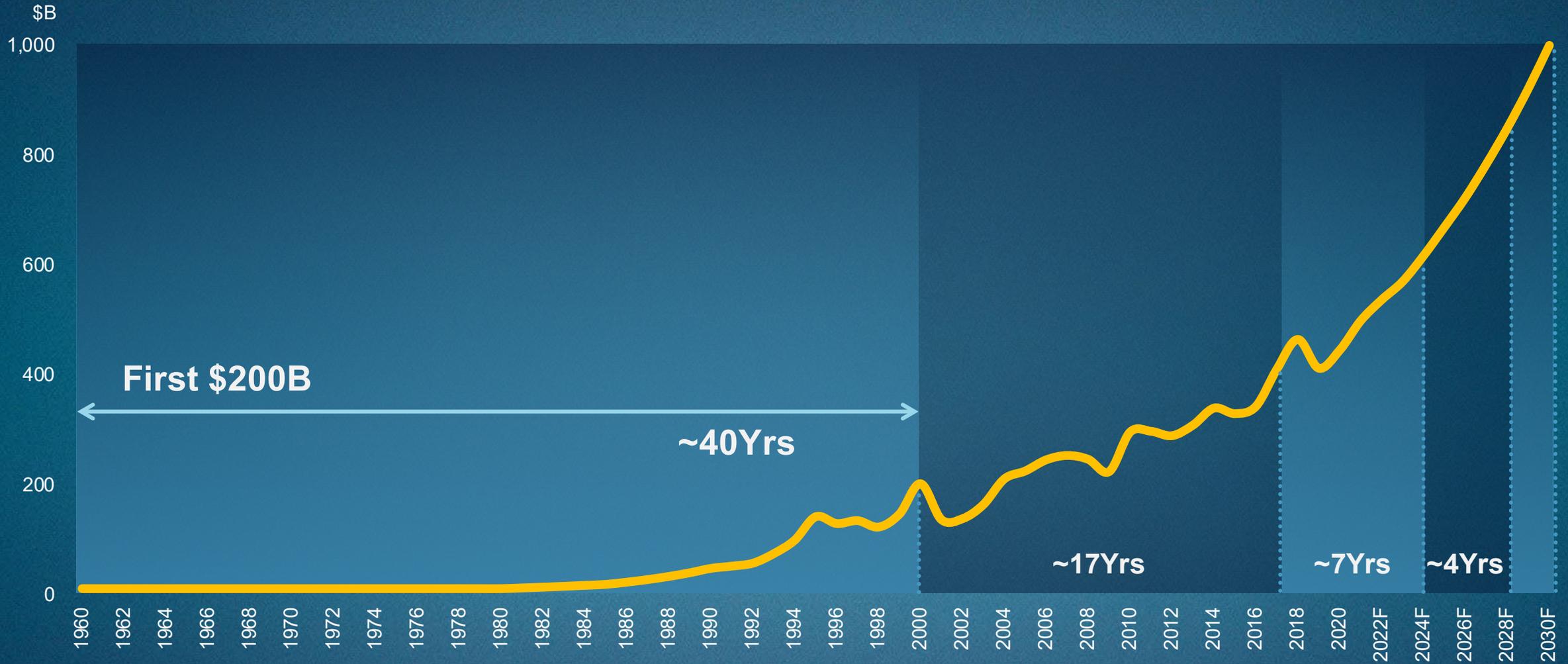
Semi content per unit		2015	2020	2025F
	HIGH END SMARTPHONE	\$100	\$170	\$275
	AUTO (GLOBAL AVERAGE)	\$310	\$460	\$690
	DATACENTER SERVER (CPU + ACCELERATOR)	\$1,620	\$2,810	\$5,600
	SMARTHOME (GLOBAL AVERAGE)	\$2	\$4	\$9

SILICON CONTENT GROWING AS EVERYTHING GETS SMARTER

Source: Applied Materials

Applied Materials External Use

Semiconductor Industry Revenues



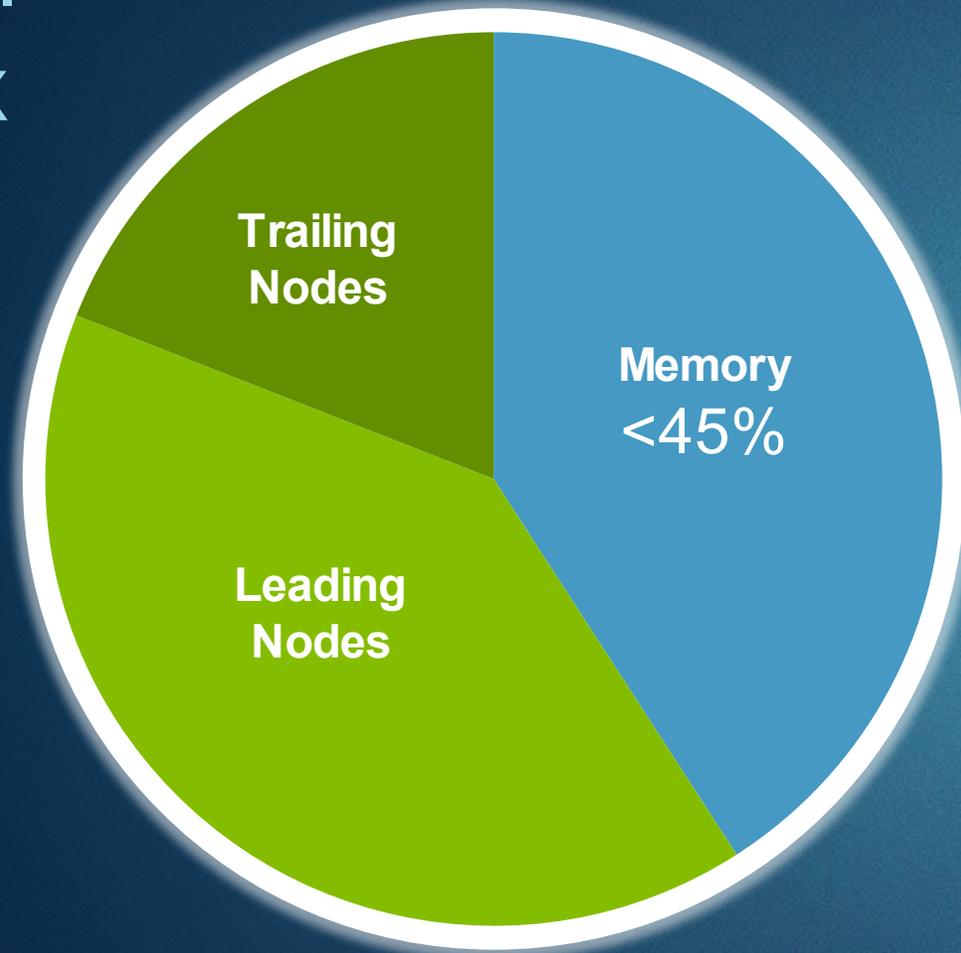
ACCELERATING TREND OVER TIME

Source: SEMI, VLSI, Applied Materials

Applied Materials External Use



Historical WFE Mix



10-Year Average

Foundry / Logic vs. Memory mix consistent over time

- 10-year and 20-year averages: Foundry / Logic >55%
- Foundry / Logic 10-year average: Leading nodes ~2/3
Trailing nodes ~1/3



ICAPS and Packaging Technology

Sundar Ramamurthy, Ph.D.

Group Vice President

GM Epi, ICAPS and Packaging

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Applied = PPACT Enablement Company™

Unit process
leadership and
broadest portfolio



Unique
combinations
of technologies

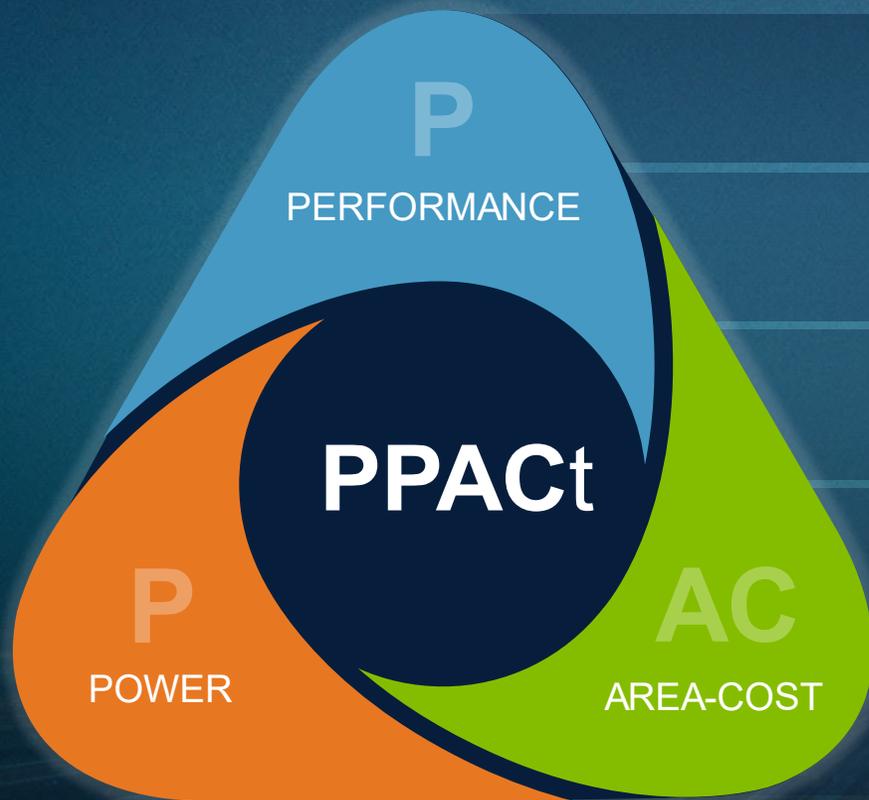


Actionable insight /
time to market
acceleration

MASTER
CLASSES

ICAPS & Advanced Packaging
Today

Process Control & AppliedPRO™
Oct 18



ENABLED BY

New architectures

New structures / 3D

New materials

New ways to shrink

Advanced packaging

Time-to-Market

NEW INDUSTRY PLAYBOOK
FOUNDATION IS MATERIALS ENGINEERING

ICAPS & ADVANCED PACKAGING



ICAPS

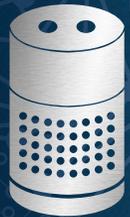
Michael Chudzik, Ph.D.
Vice President of Technology



ADVANCED PACKAGING

Nirmalya Maity, Ph.D.
Corporate Vice President
Advanced Packaging

TETHERED
EDGE



BATTERY
EDGE



EDGE
DATA CENTER



ICAPS NODES



COMMUNICATIONS



CLOUD DATA CENTER

LEADING EDGE

Unique Product Portfolio + Integrated Solutions

CREATE
Materials deposition



Epitaxy



Metal
Deposition



Dielectric
Deposition



Plating



ALD



Selective
Deposition

SHAPE
Materials removal



Etch



Planarization



Selective Removal

MODIFY
Materials modification



Implant



Thermal



Treatments

ANALYZE
Materials analysis



Optical Inspection



Defect Review



eBeam Inspection



CD-SEM

**SOLUTIONS &
CONNECTED
PRODUCTS**



IMS



ICAPS



Packaging



Applied AIx™

Only company with
Process + metrology
Full flow chip lab
Full flow packaging lab
META R&D accelerator

Unique combinations
Breadth enables linking
capabilities in new ways

ICAPS

IoT

Comms

Auto

Power

Sensor





September 8, 2021:

“New Applied Materials Technologies Help Leading Silicon Carbide Chipmakers Accelerate the Transition to 200mm Wafers and Increase Chip Performance and Power Efficiency”

Accelerating Power Technology Roadmap



Gregg Lowe

President and CEO, Cree, Inc.

“*Electrification of the transportation industry is a rising trend, and we are accelerating this inflection point by leading the global transition from silicon to silicon carbide with our Wolfspeed technology. Delivering the highest-performing silicon carbide power devices on larger 200mm wafers enables us to increase end-customer value and meet growing demand. **Applied's support in helping speed qualification of 200mm processes in Albany and multi-equipment installations at our Mohawk Valley Fab is expediting this transition. Moreover, new technologies being developed by Applied's ICAPS team, such as hot implant, have broadened and deepened our technical collaboration and helped accelerate our power technology roadmap.***”

ICAPS Materials Engineering Challenges and Opportunities

Michael Chudzik, Ph.D.

Vice President of Technology
Semiconductor Products Group

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BIGGEST

Computing Wave Yet

“IoT is expected to add over \$1.1 T to the Global Economy by 2025, rising to >\$1.5T by 2030.”

The Economist / Transforma Insights



IoT – Internet of things
PC – Personal computer
AI – Artificial intelligence

Source: SEMI, VLSI, Applied Materials

A Global Competition to Win the IoT Inflection

Global Competition

“Worldwide Spending on Edge Computing Will Reach \$250 Billion in 2024”

IDC | Sep 23, 2020

“Our Wearables business is now the size of a Fortune 120 company”

Apple | Jan 27, 2021

“Microsoft earns contract worth up to \$21.9 billion to make AR devices for the US Army”

CNN | Mar 31, 2021

“Verizon and Honda want to use 5G and edge computing to make driving safer”

TechCrunch | Apr 8, 2021

“Remote monitoring of a patient’s heart and respiratory metrics is only possible with something like edge computing.”

MIT | Technology Review Jun 10, 2021

New Multi-Billion-Unit Markets



Wearable Tech



Smart Home



Mobile Computing



Industrial IoT



Health Care



Smart Auto



AR / VR



Green Energy



Edge Networks



Surveillance



Agriculture



Smart Cities

Enabled by Semi Innovations



Image Sensor



Power Devices



RF Devices



Analog Devices



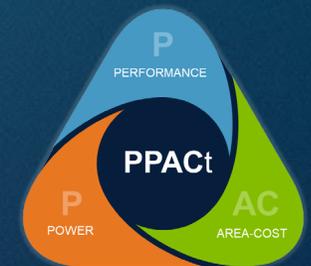
MEMS Devices



Photonics



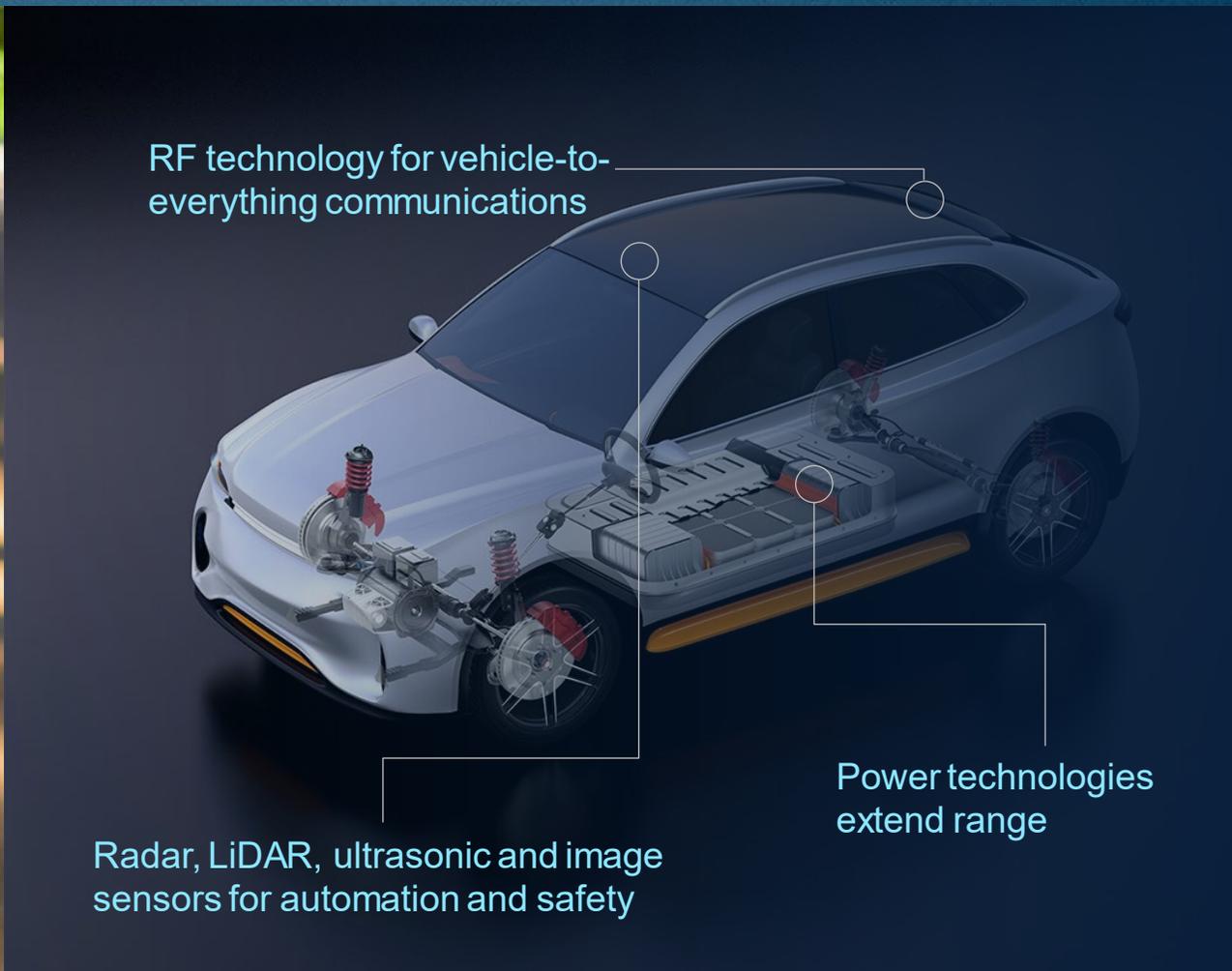
Edge CMOS



IoT – Internet of things
AR / VR – Augmented / virtual reality
RF – Radio frequency

MEMS – Microelectromechanical systems
CMOS – Complementary metal-oxide-semiconductor

Innovative ICAPS Technologies Transforming the Edge



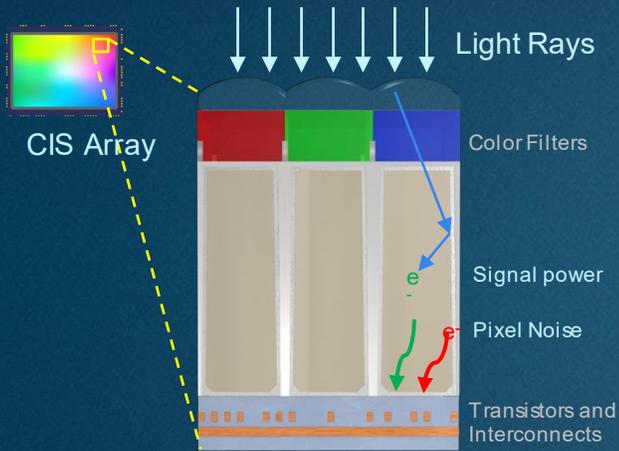
CIS – CMOS image sensor
MEMS – Microelectromechanical systems

NFC – Near-field communication
RF – Radio frequency

Image Sensor Physics and Implications for Performance

CMOS image sensor

Electrons generated in a silicon photodiode (pixel) are measured against background noise



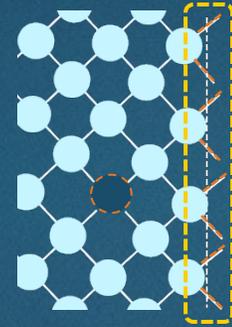
Performance is determined by the ratio of signal to noise (SNR)

$$SNR \sim \frac{\text{Signal Sensitivity}}{\text{Pixel Noise}} \propto \frac{(i_{ph}t_{int})^2}{q(i_{ph}+i_{dc})t_{int}}$$

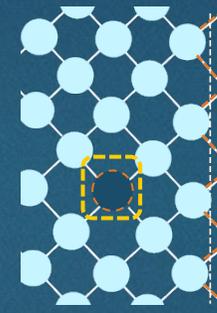
i_{ph} : photocurrent (signal) q : electron charge
 t_{int} : integration time i_{dc} : dark current (noise)

Pixel noise reduction

$$SNR \sim \frac{\text{Signal Sensitivity}}{\text{Pixel Noise} \sim i_{dc}}$$



Surface damage

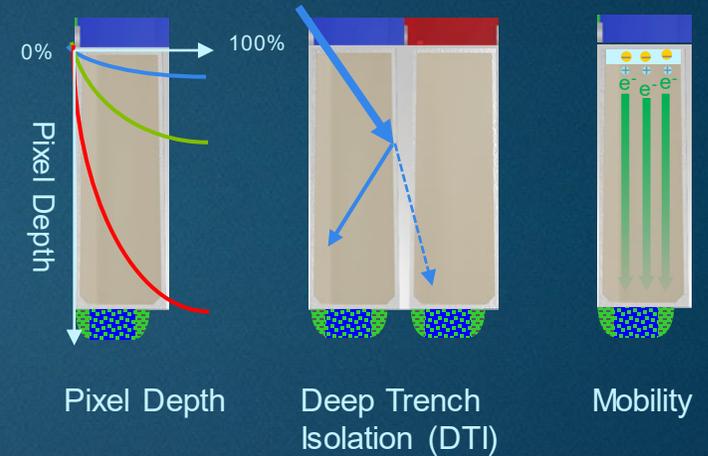


Crystal Damage

$i_{dc} \downarrow$ Surface damage = Interface engineering
 Crystal damage = Crystal reconstruction

Signal sensitivity improvement

$$SNR \sim \frac{\text{Signal Sensitivity} \sim i_{ph}}{\text{Pixel Noise}}$$

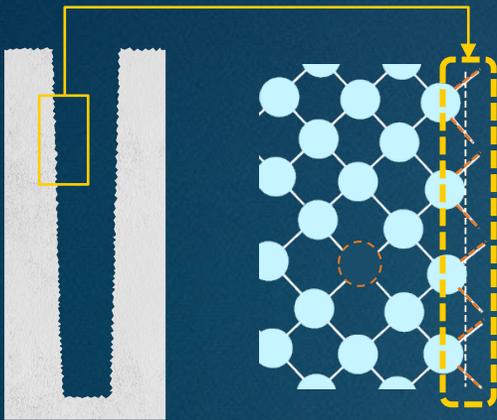


$i_{ph} \uparrow$ Deeper Pixel = Deeper silicon trenches
 New DTI materials = High reflectance
 Higher mobility = Interface / bulk quality improvement

Reducing Pixel Noise with Surface Engineering

High-value problem

Defect sites at the pixel surface are sources of pixel noise



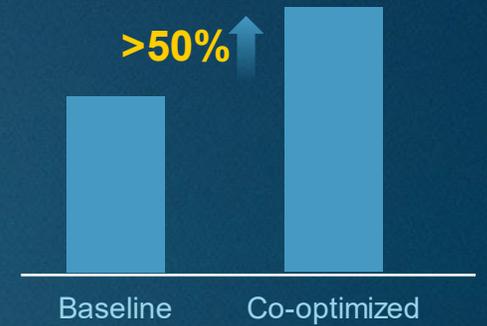
Solution

Low-damage etch followed by silicon regrowth with embedded charge sites for defect passivation

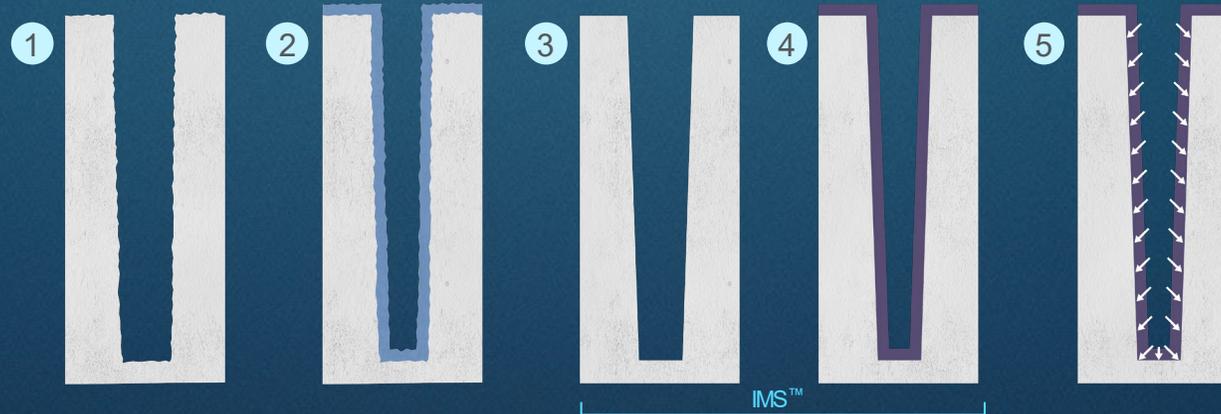
DTI surface engineering module

- ① Lower damage silicon etch
- ② Sidewall oxidation consumes damage layer
- ③ Selective removal of oxide
- ④ Doped epitaxial silicon regrowth
- ⑤ Millisecond anneal embeds passivating charges

Device value SNR



$$SNR \sim \frac{\text{Signal Sensitivity}}{\text{Pixel Noise} \sim i_{dc}}$$



Products co-optimized

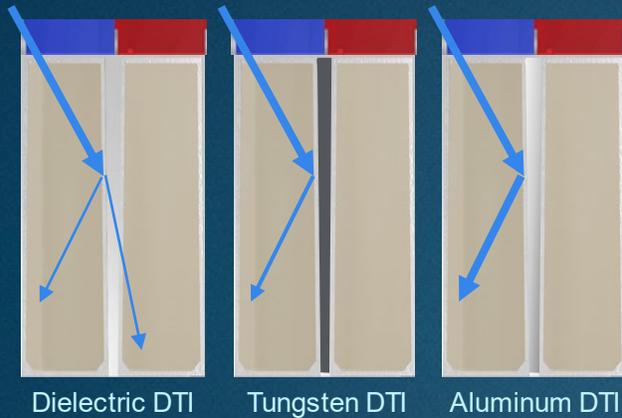
Centris® Sym3® Via Etch
 Centura® RPO
 Centura® RP Epi with Siconi®
 Vantage® Astra® DSA

SNR – Signal-to-noise ratio
 DTI – Deep trench isolation
 IMS – Integrated materials solution
 RPO – Remote plasma oxidation
 RP – Reduced pressure
 DSA – Dynamic surface anneal

Improved Signal Sensitivity with New Materials for DTI

High-value problem

Signal sensitivity is degraded when incoming light escapes the pixel or is absorbed by the blocking layer



Solution

DTI created with a highly reflective aluminum layer co-optimized with pre- and post- processes to maximize signal current

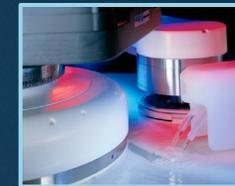
DTI aluminum reflectance module

1 ALD Liner + CVD Al deposition

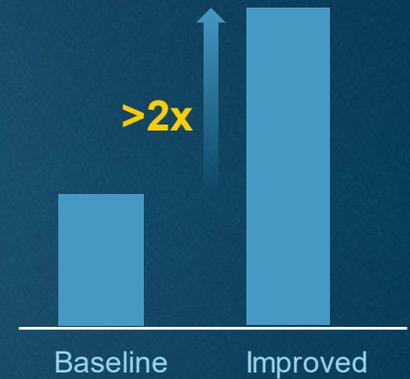


IMS™

2 Aluminum Planarization

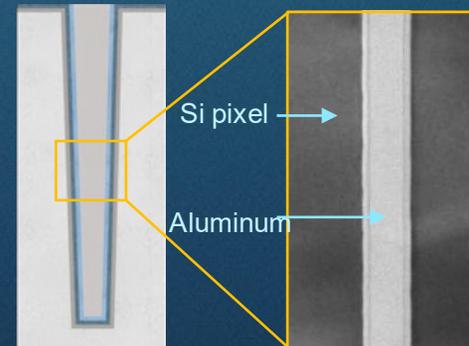


Quantum efficiency



	Technology	Light Blocking	Light Reflecting
Gen 1	Dielectric Refraction	● ● ●	● ● ●
Gen 2	Tungsten Metal Blocking	● ● ●	● ● ●
Gen 3	Aluminum Metal Reflectance	● ● ●	● ● ●

ALD Liner + CVD Al inside DTI



Products co-optimized

Endura® CVD Al
Reflexion® LK CMP

DTI – Deep trench isolation IMS – Integrated materials solution
ALD – Atomic layer deposition CVD – Chemical vapor deposition

Transition to EV with adoption of ADAS increases ICAPS semiconductor content by 4x

Internal Combustion Engine¹

Electric Vehicle²



~\$500 Total cost
47% Power & Sensors

~\$2,000 Total cost
58% Power & Sensors

EV – Electric vehicle
 ADAS – Advanced driver-assistance systems

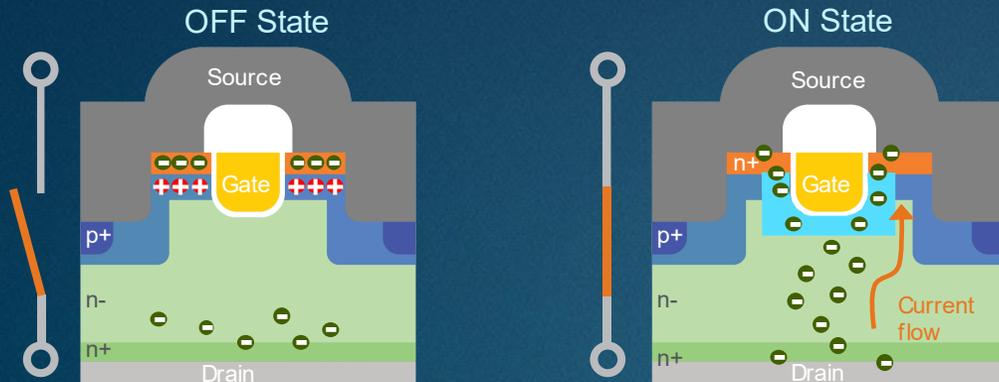
CIS – CMOS image sensor
 CMOS – Complementary metal-oxide-semiconductor

1 Based on ADAS L2 Content
 2 Based on ADAS L4/5 Content
 Source: Infineon ATD report, 2015, 2020

Power Device Physics and Implications for Performance

Power MOSFET

A high-voltage, high-current semiconductor switch



Most critical challenge is to reduce power losses in the switch

$$\text{Power Dissipation} = I_D^2 \cdot R_{ON}$$

$$R_{ON} = \frac{w_D}{q\mu_n N_D}$$

I_D : Drain current
 R_{ON} : On resistance
 w_D : Depletion region width
 q : Proton charge
 μ_n : Electron mobility
 N_D : Dopant concentration

MOSFET – Metal-oxide-semiconductor field-effect transistor

Improving power MOSFET performance

↓ R_{ON}

Increase mobility μ_n

Material selection (Si, SiC, GaN), crystal orientation
 Minimize crystal defects in the bulk or at the surface

Increase dopant concentration N_D

Implant dose / minimizing implant crystal damage

Tradeoff between performance and cost

	Si	SiC	GaN
Breakdown Voltage	1x	10x	25x
Device Efficiency	● ● ●	● ● ●	● ● ●
Relative Die Size	10x	1x	≤ 1x
Wafer Cost (size)	\$30 (6")	\$800 (6")	\$1200 (4")
% Contribution to Market Growth ('20-'26)	36%	48%	16%

Applied Materials estimates, Yole Developpement and Omdia

Reducing Surface Defects | Why This is Difficult

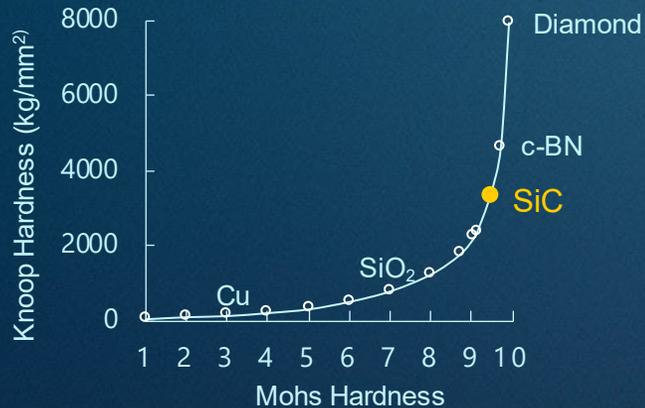
High-Value Problem

Electron mobility is degraded by crystal defects originating from the SiC substrate



O. Kordina, Silicon Carbide Epitaxy, 2012

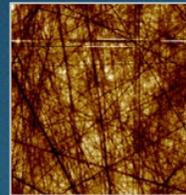
Hardness of SiC makes polishing extremely challenging



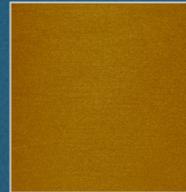
Solution

Single-wafer CMP with higher down force and optimized consumables to minimize surface defects

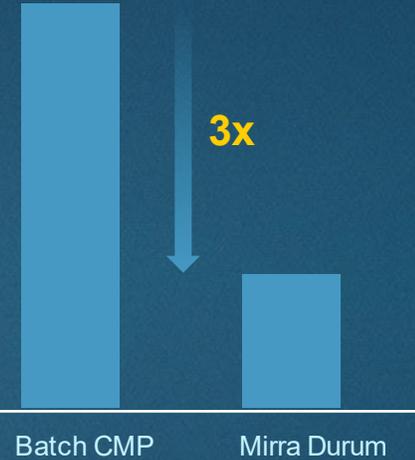
Pre-CMP
High density
of scratches



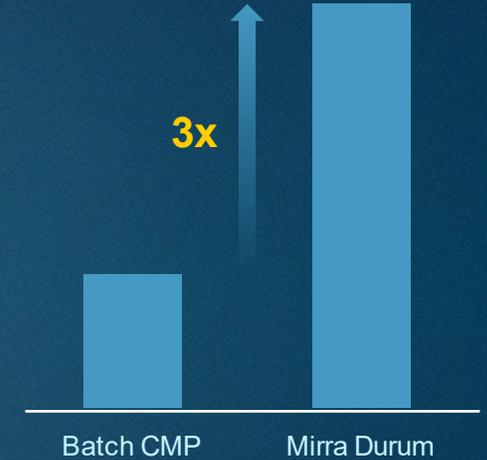
Post-CMP
Scratch-free



Average roughness



Material removal rate



Mirra® Durum™ CMP

- Highest productivity single-wafer multi-platen polisher for SiC
- Processes both 150mm and 200mm wafers
- Fully automated dry-in, dry-out wafer handling
- Integrated cleaning, drying and metrology

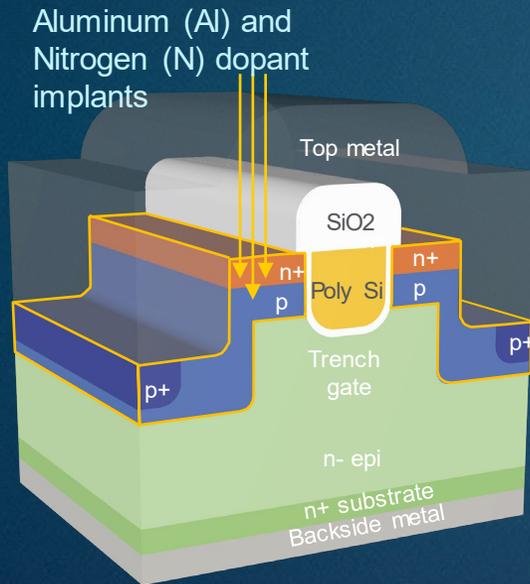
Increasing SiC MOSFET Mobility and Lowering Resistance

High-Value Problem

Bulk defects in SiC caused by implant damage reduce electron mobility

$$R_{ON} = \frac{w_D}{q\mu_n N_D}$$

I_D : Drain current
 R_{ON} : On resistance
 w_D : Depletion region width
 q : Proton charge
 μ_n : Electron mobility
 N_D : Dopant concentration

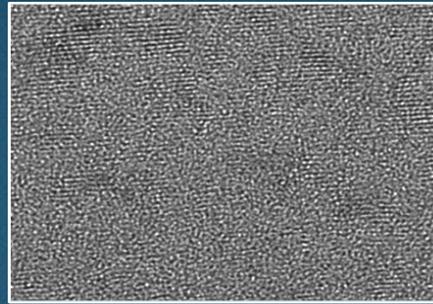


Conventional implanting of dopants damages the crystal lattice

Solution

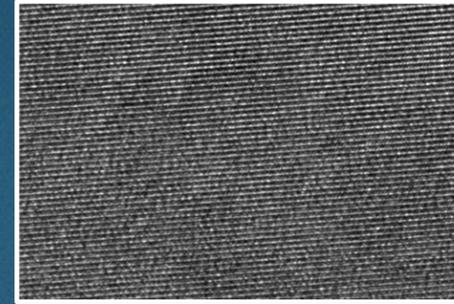
Room-temperature implant damages crystal; hot implant allows crystal damage to heal, reducing R_{ON}

Amorphized structure
 Damaged



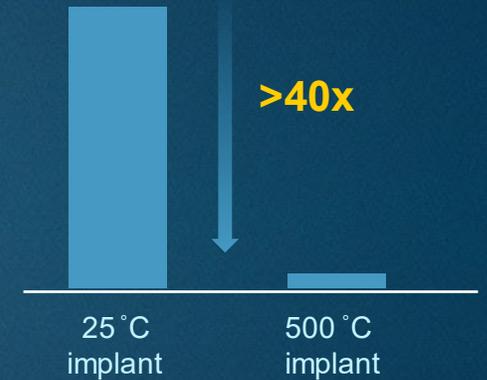
25 °C implant

Crystallized structure
 Healed



500 °C implant

Resistivity*



VISta® 900 3D

- Highest productivity implanter for 150mm and 200mm SiC
- Hot implant capability for bulk damage reduction
- Tilted implant for next-generation SiC device architectures
- Solid dopant Al ion source for lowest maintenance time

* Post 1600°C Anneal

Organized to Address ICAPS Opportunities

Unit process leadership and broadest portfolio



Unique combinations of technologies



Time-to-market acceleration



Metal Deposition



Epi



Implant



Etch



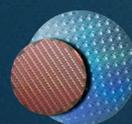
Planarization



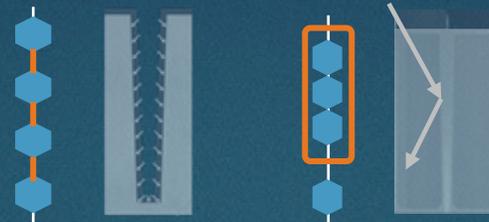
Inspection



Dielectric Deposition



Various Wafer Sizes



Co-optimization of processes / tools

Integrated materials solutions



Dedicated and partner ICAPS device labs/fabs



Device Modeling



Test Structures

Dedicated technical collaboration with our customers to accelerate their PPACT roadmaps

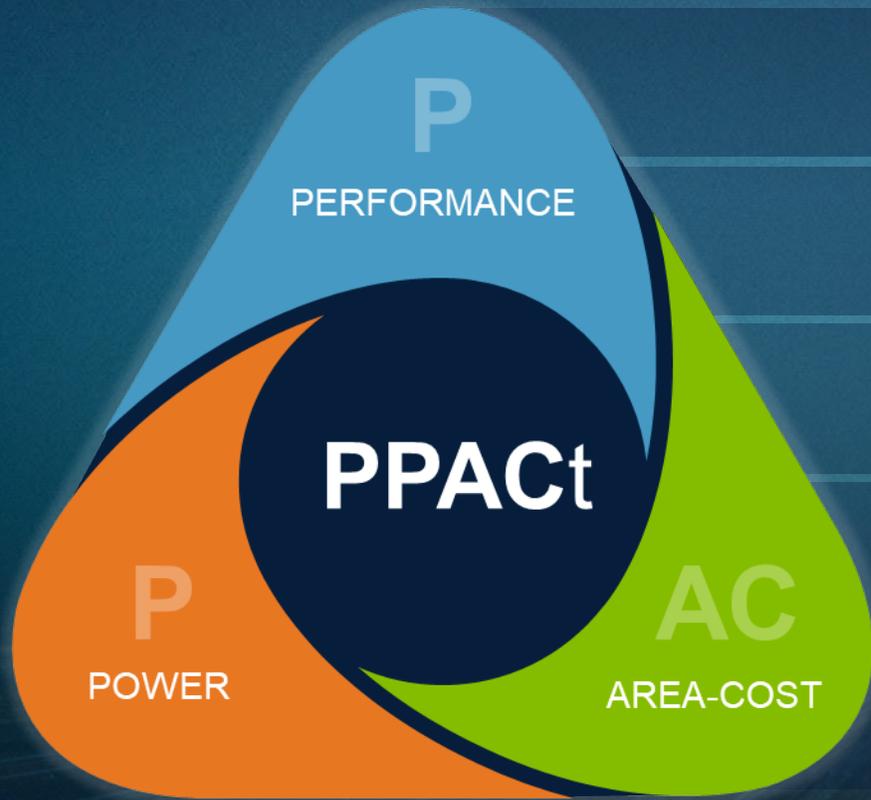


Advanced Packaging Challenges and Opportunities

Nirmalya Maity, Ph.D.

Corporate Vice President Advanced Packaging

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ENABLED BY

New architectures

New structures / 3D

New materials

New ways to shrink

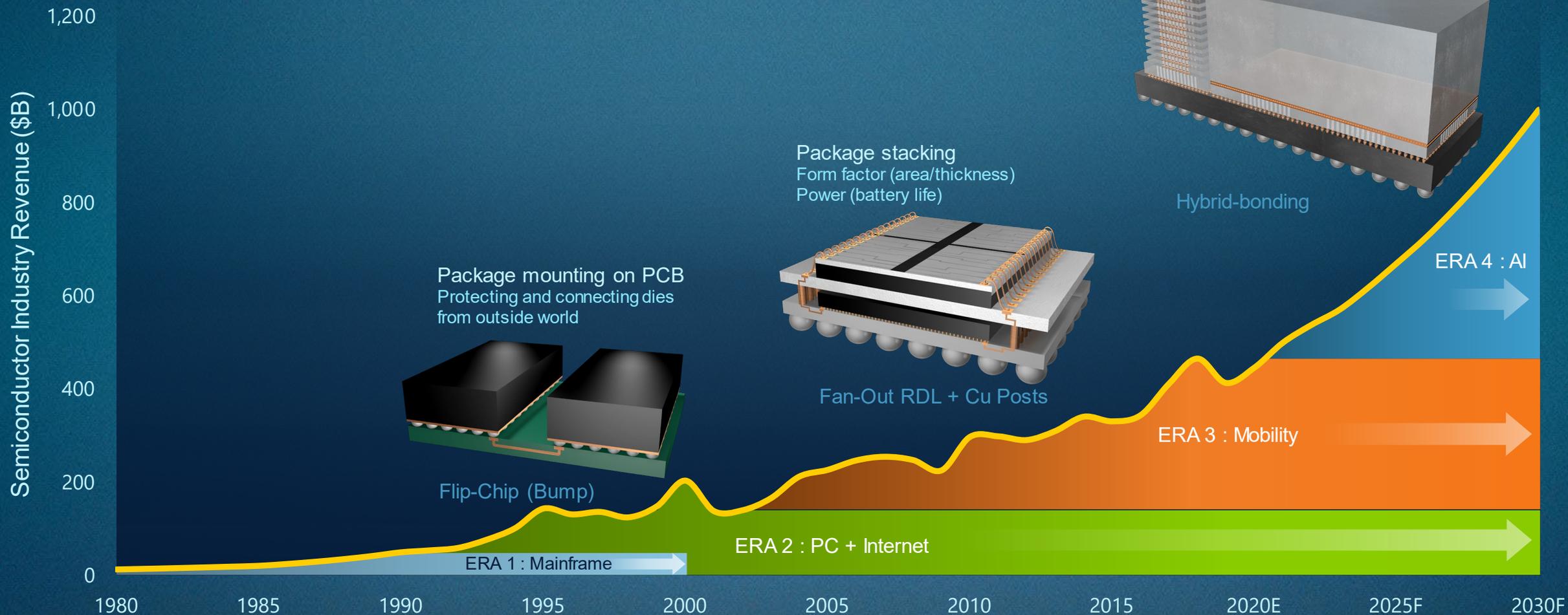
Advanced packaging

Time-to-Market

NEW INDUSTRY PLAYBOOK
FOUNDATION IS MATERIALS ENGINEERING

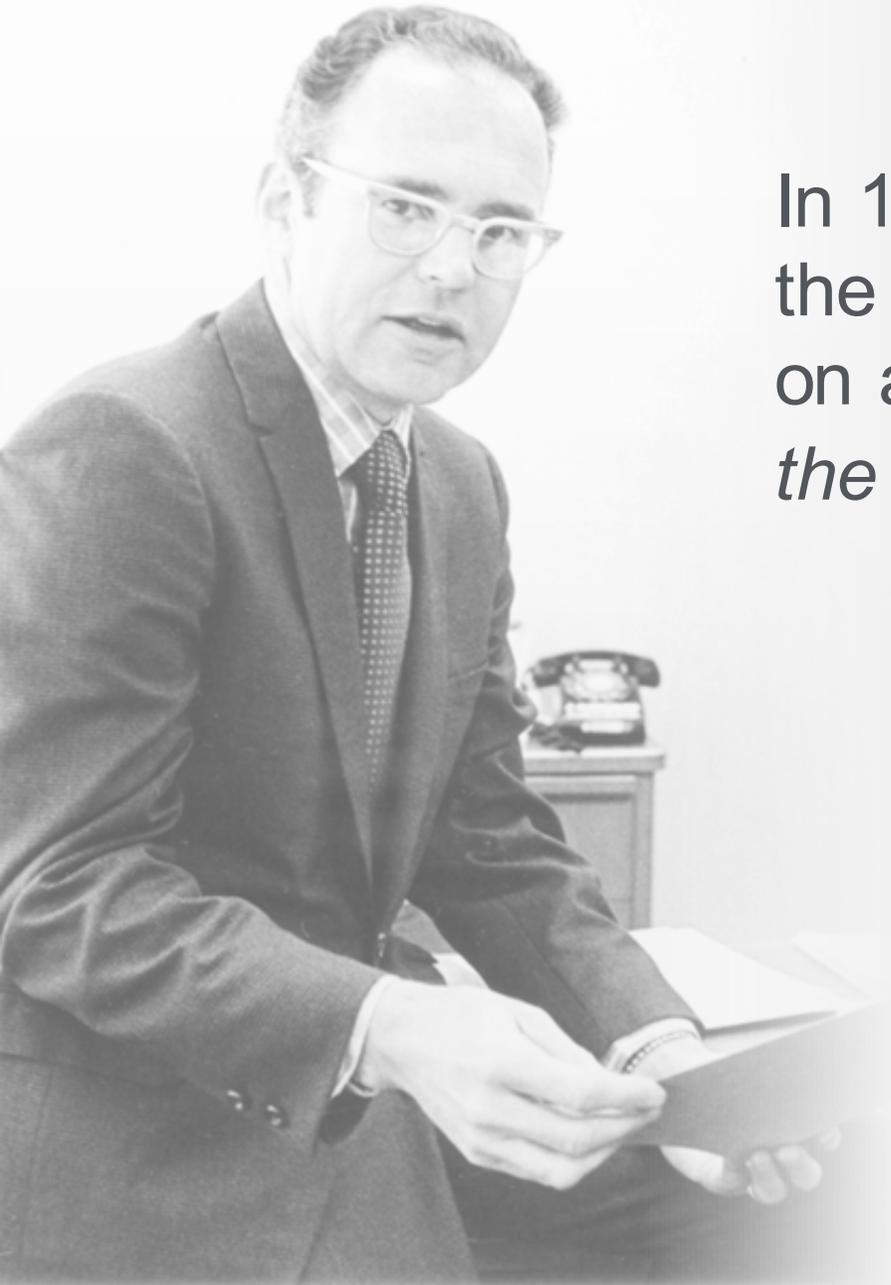
BIGGEST

Computing Wave Yet



Source: SEMI, VLSI, Applied Materials

Applied Materials External Use



In 1965, Gordon Moore predicted both the exponential increase of transistors on a chip, and conditions that would drive *the disaggregation of the system-on-chip*

“ It may prove to be more economical to build large systems out of smaller functions, which are separately packaged and interconnected ”

Packaging Enables PPACT™ Scaling

Power

Shorter, parallel interconnects

Higher I/O

Reduced latency

Lower power



30x lower power

PCB chip-to-chip connection
vs. hybrid bonding

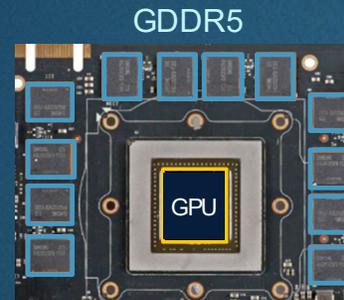
Performance

3D stacking

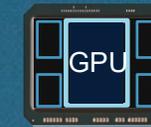
Tighter integration

Many chips per package

High bandwidth



HBM



~3X system performance

>50% lower power

Compared to disaggregated dies on a PCBs

Source: Samsung whitepaper

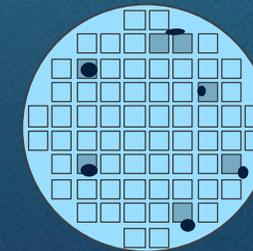
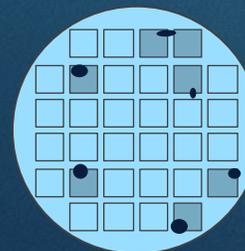
Cost

time-to-market

Chipselets

Higher yield

Reuse IP blocks



~60% lower cost

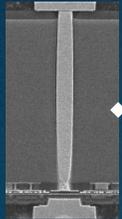
vs. 900mm die partitioned
into 3 and 3D stacked

Compared to large and specialized SOC chips

Source: A. Steengen, IMEC (Semicon Korea 2018)

System Integration with Emerging 2D and 3D Interconnects

THROUGH-SILICON VIA (TSV)



MICRO-BUMP

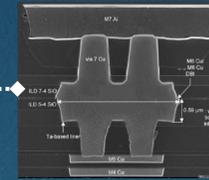


ADVANCED SUBSTRATE



Image Sources: SystemPlus Consulting Reports

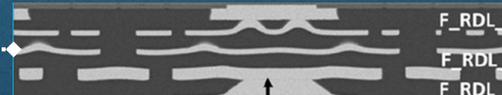
HYBRID BONDING



Source: TechInsights (Chipworks) IMX260 Camera Module Report, 2016

FLIP-CHIP BUMP

POLYMER RDL / Si INTERPOSER



3D Interconnects

- Through-Silicon Via (TSV)
- Hybrid bonding¹

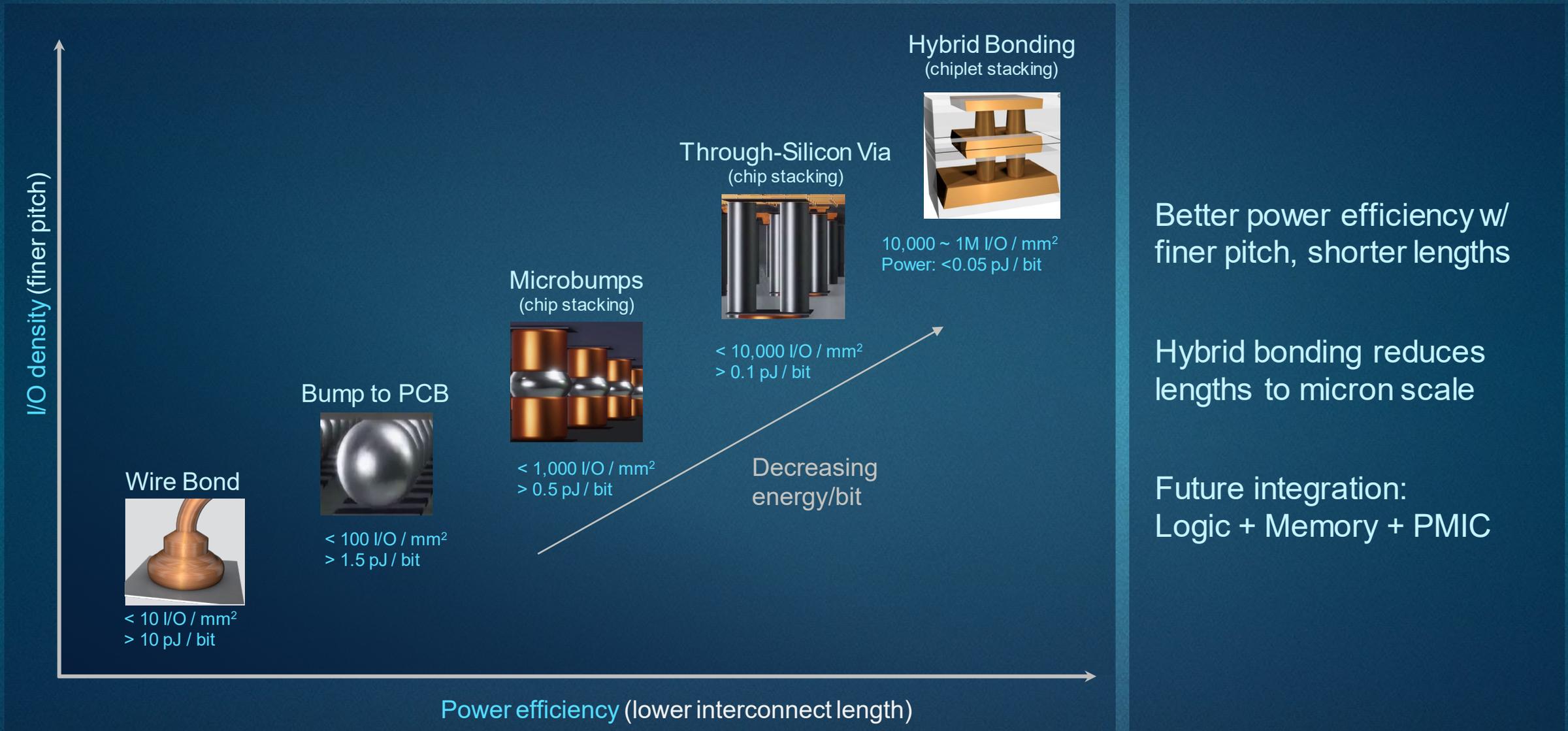
2D Interconnects

- Redistribution layer (RDL) on wafer or panel¹
- Advanced substrate¹

¹ Emerging inflection

Multiple inflections + higher process complexity, needs broad technology portfolio and integrated solutions

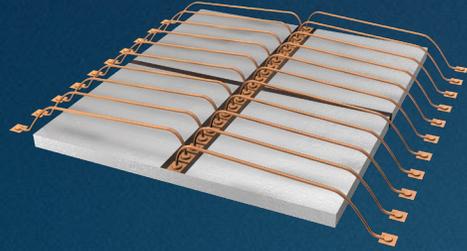
Packaging System Interconnect Scaling Roadmap



Packaging to Enable Higher Density and Performance

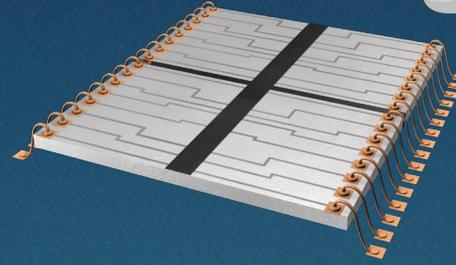
Top View

Connections initiate from DRAM die center



Single or two die wire-bonded onto package

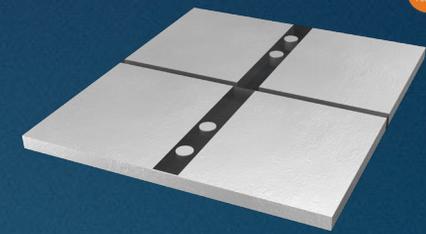
Redistribution layer routes connections to edge



2-4 die on package
Aluminum RDL and wire-bonded



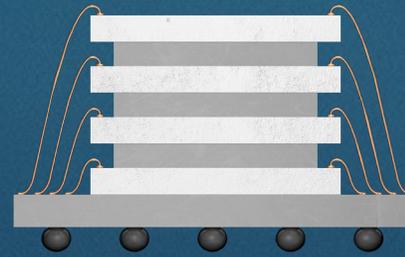
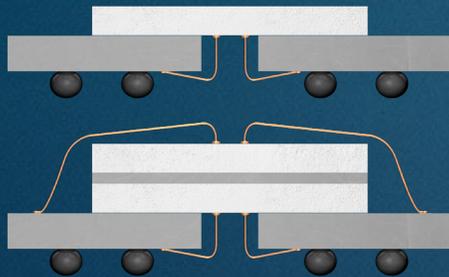
TSV routes connections through silicon die



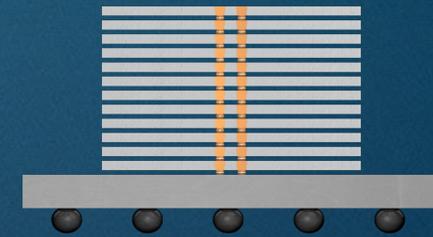
4+ die on package
Connected by TSVs and micro-bumps



Side View



Enabling technologies
Endura® PVD



Enabling technologies
TSV and micro-bump processes

3X growth in DRAM wafers using advanced schemes like flip-chip, stacking or TSV stacking by 2025

Source: Applied Materials estimates

Through-Silicon Via Fabrication and Backside Reveal

TSV Formation



Centris® Sym3® Via Etch



Producer® InVia® CVD



Endura® Ventura® PVD



Nokota® Raider® ECD



Reflection® LK CMP



Incoming Wafer



TSV Etch Bottom Open (Via Last)



CVD Liner



PVD Barrier and Seed



TSV Cu Plating



Planarize Remove Cu/Barrier

Backside Reveal



Reflection® LK CMP



Centris® Sym3® Via Etch



Producer® InVia® CVD



Reflection® LK CMP



Thinned Wafer



Silicon Polish



Recess Etch



CVD Passivation

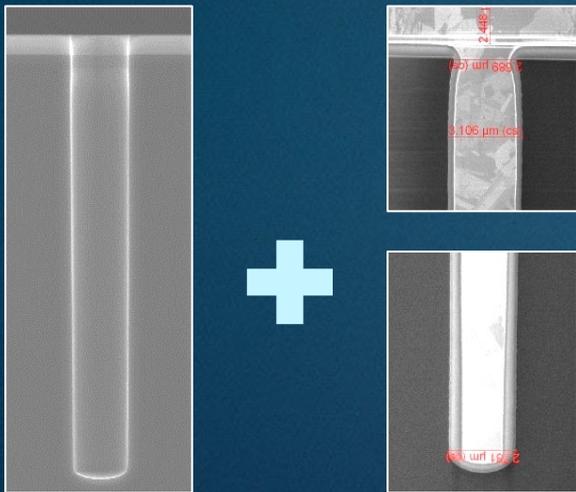


Copper & Oxide Polish

Redistribution Layer & Bump/Fan-Out

Solving TSV Extendibility Challenges

Electrical Isolation at Low Temperatures

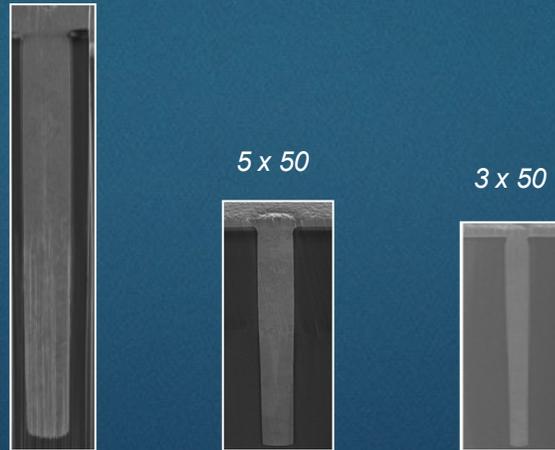


Smooth silicon sidewall and high-quality dielectric liner

Complete TSV Fill with Copper

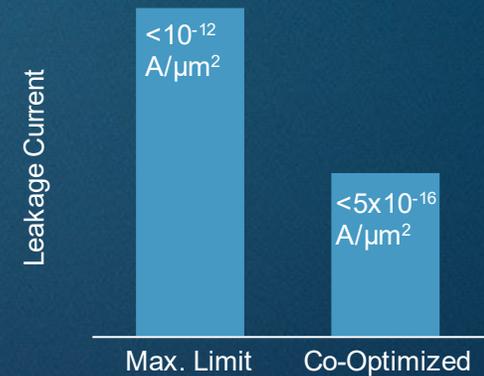
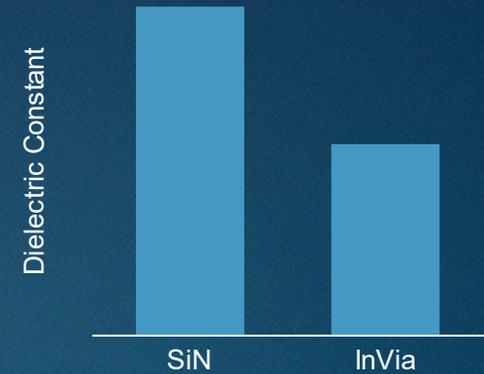


10µm x 100µm



Co-optimization of PVD liner and ECD fill for robust TSV gap-fill extendable to 3x50 vias

Co-Optimizing Processes

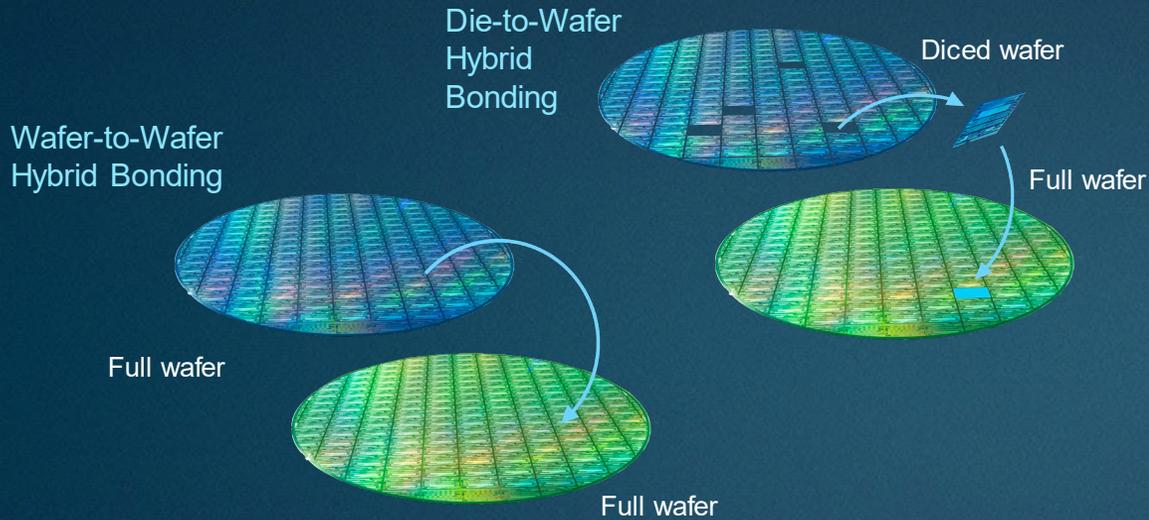


Electrically robust solution

Hybrid Bonding: Enabling 10K-1M/mm² I/O Density Paradigm

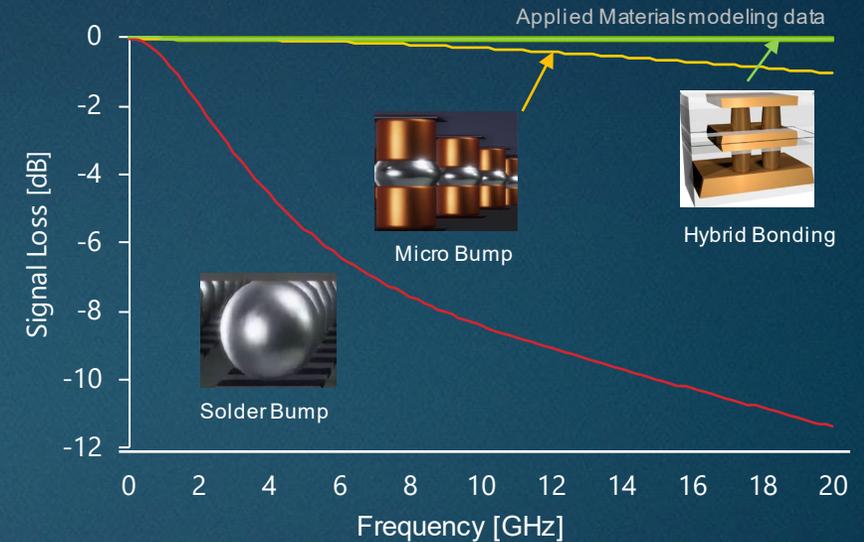
What is hybrid bonding?

Shortest connections with face-to-face chip bonding



The potential of hybrid bonding

Ultimate bonding solution – outstanding performance



The challenge

Making over 10,000 connections simultaneously with defect-free copper bonding

Die-to-wafer and wafer-to-wafer alignment – at an economical cost

Enabling hybrid bonding in collaboration with Besi die-to-wafer and EVG for wafer-to-wafer

Optimization of Complete Process for Highest Bonding Yield

Pad Formation: current Applied Materials product portfolio

+

Bonding: in partnership

Producer® CVD



Dielectric stack
CVD

Producer® Etch



Damascene RDL /
pad formation etch

Endura®



Barrier / Seed PVD

Mustang®



Copper pad fill
ECD

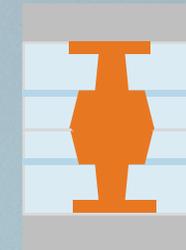
Reflexion® LK



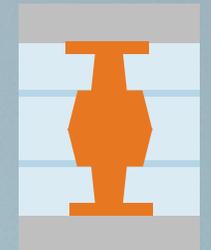
CMP with tuned
dishing control



Surface
preparation



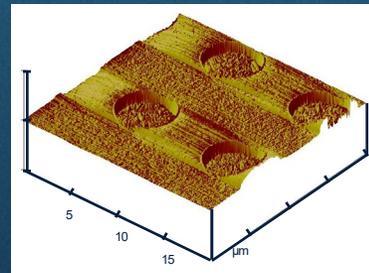
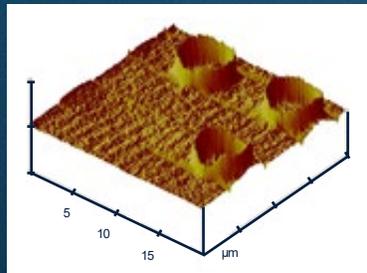
Pick-and-place, attach
(D2W or W2W)



Anneal and finish
bonding

Engineered surface profile

- ① Material polish rate differences
- ② Optimized copper pad recess



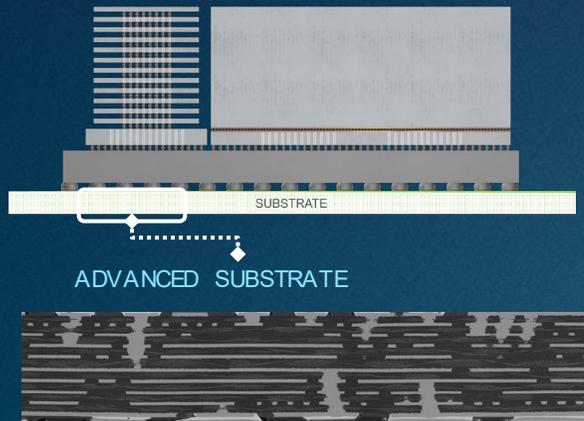
Surface preparation and bonding

- ① Edge delamination
- ② Large void
- ③ μ -void



Processing Large Packages and Substrates

System integration of multiple chips on package

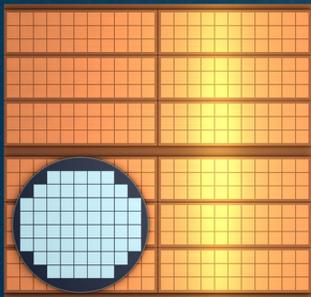


Panel-level packaging
Package size grows

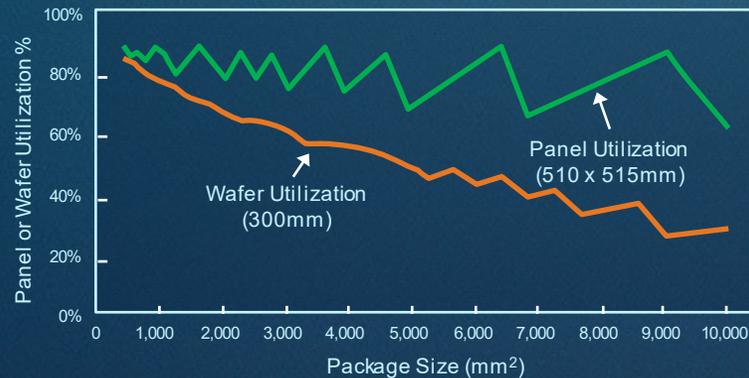
Semi quality processing
Higher I/O density requires
interconnects to shrink

Image Sources: SystemPlus Consulting Reports

Better substrate utilization as package sizes increase



Source: Intel



Advanced large substrate PVD technology



Applied Topaz™ PVD

Acquisition of Tango Systems
Panel PVD technology

Panels up to 600x600mm
Thin panel handling capability

Leveraging decades of Applied PVD technology leadership in both semiconductor and large format display businesses

Enabling fine-line interconnects in large-format packaging substrates

Organized to Address Packaging Challenges

Unit process leadership and broadest portfolio



Focus on enabling valuable inflections



Co-optimized technologies



Metal Deposition



Dielectric Deposition



Plating



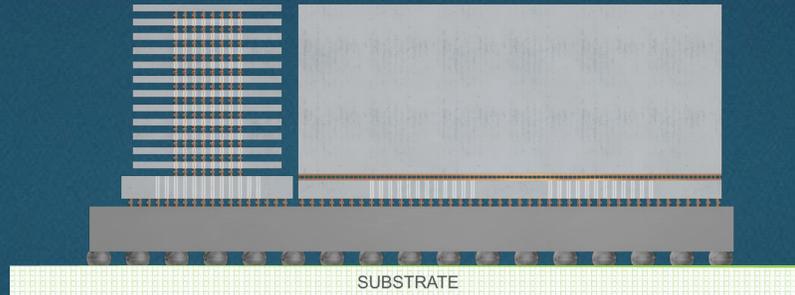
Etch



Planarization



Inspection

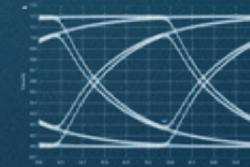


Heterogeneous Integration

Advanced Substrates



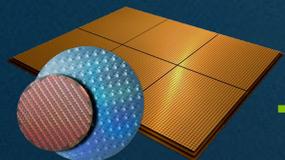
Dedicated advanced packaging lab



Package modeling



Test vehicles



Wafer and Panel



Partnerships

Uniquely positioned to capture growth from inflections



ICAPS and Packaging Growth Opportunities

Sundar Ramamurthy, Ph.D.

Group Vice President

GM Epi, ICAPS and Packaging

ICAPS and PACKAGING MASTER CLASS | September 8, 2021

Going Beyond Unit Process Tools to Deliver Solutions



UNIT PROCESS LEADERSHIP
+ BROADEST PORTFOLIO

FASTER TIME TO MARKET, HIGHER VALUE, STICKIER



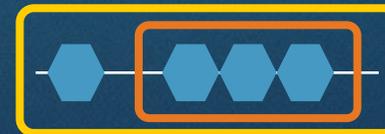
CO-OPTIMIZATION OF
PROCESSES / TOOLS

~40% of our products
now co-optimized



INTEGRATED
MATERIALS
SOLUTIONS

~30% of our products
now integrated



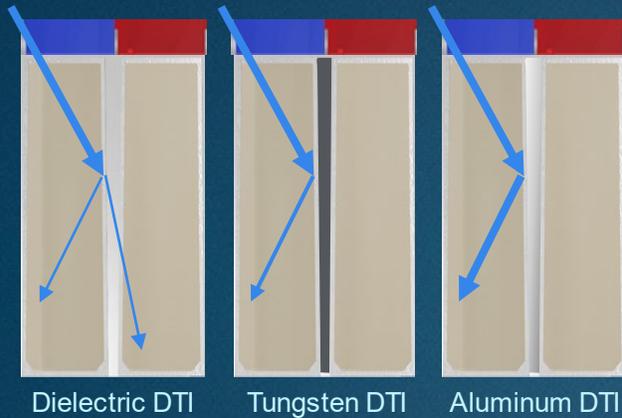
SENSORS + eBeam + AI / ML

ACTIONABLE INSIGHT
ACCELERATION

Improved Signal Sensitivity with New Materials for DTI

High-value problem

Signal sensitivity is degraded when incoming light escapes the pixel or is absorbed by the blocking layer



Solution

DTI created with a highly reflective aluminum layer co-optimized with pre- and post- processes to maximize signal current

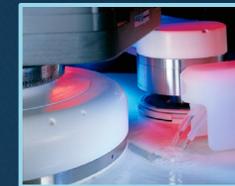
DTI aluminum reflectance module

1 ALD Liner + CVD Al deposition

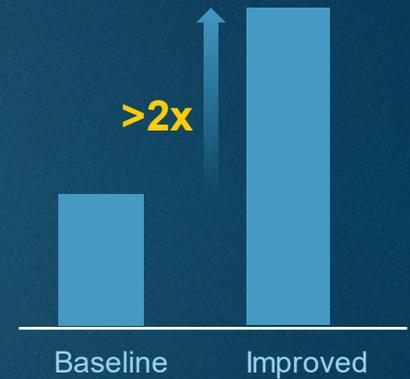


IMS™

2 Aluminum Planarization

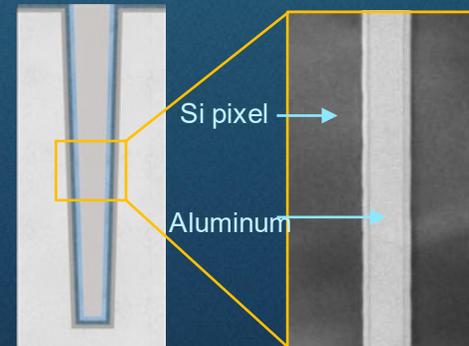


Quantum efficiency



	Technology	Light Blocking	Light Reflecting
Gen 1	Dielectric Refraction	● ● ●	● ● ●
Gen 2	Tungsten Metal Blocking	● ● ●	● ● ●
Gen 3	Aluminum Metal Reflectance	● ● ●	● ● ●

ALD Liner + CVD Al inside DTI



Products co-optimized

Endura® CVD Al
Reflexion® LK CMP

DTI – Deep trench isolation IMS – Integrated materials solution
ALD – Atomic layer deposition CVD – Chemical vapor deposition

New Materials Co-Optimized to Improve CIS Capabilities

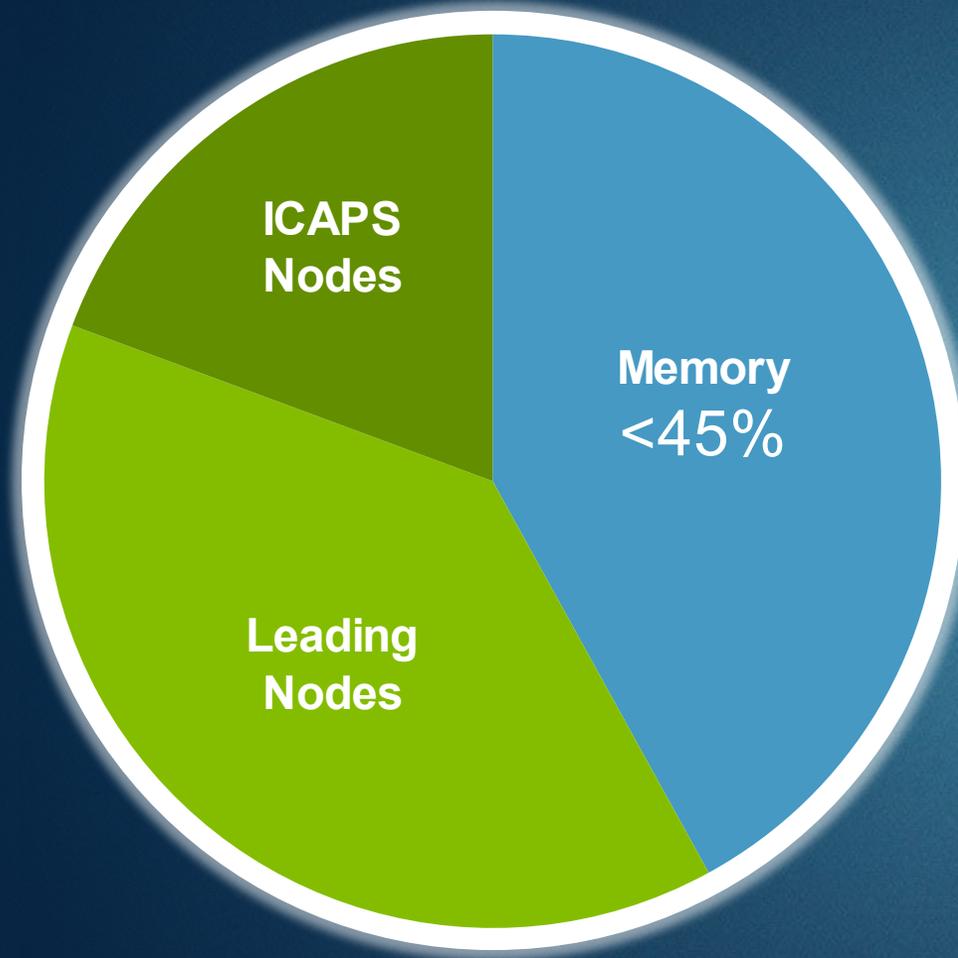


Terushi Shimizu

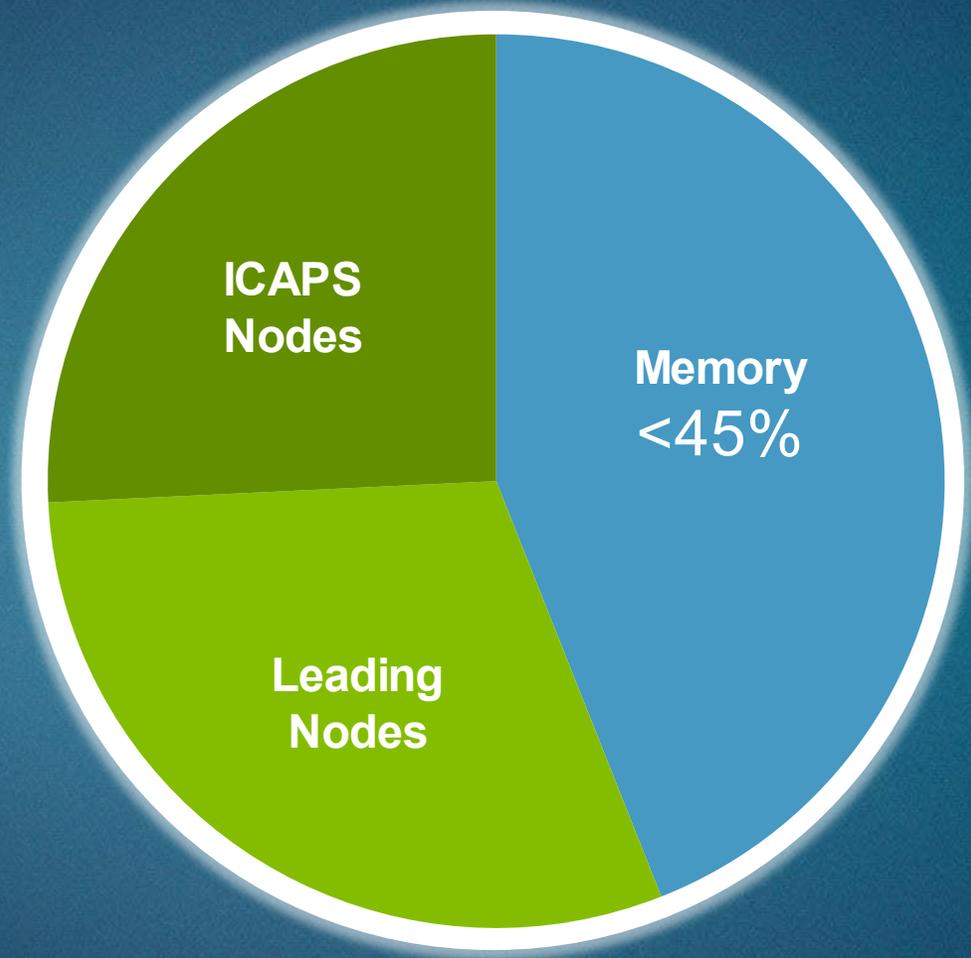
President and CEO
Sony Semiconductor Solutions
Corporation

“ *Image sensors with AI functionality are going to change how we engage with the world around us. At the heart of this is Sony’s CMOS sensor, where innovations in process technologies are required to improve performance attributes such as sensitivity, resolution and dynamic range. **Applied Materials has created new materials solutions that are co-optimized with their broad equipment portfolio, which allows Sony to continue to improve image sensor capabilities.** ”*

WFE Mix



10-Year Average



2018-2021e

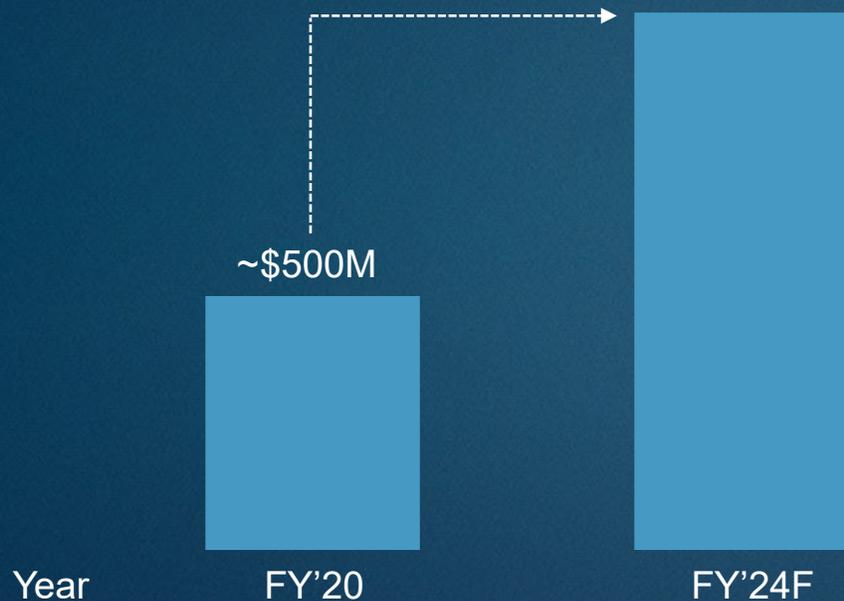
■ = memory, ■ = foundry-logic

Source: Gartner, VLSI, Applied Materials

Applied Materials External Use

Positioned for Growth in Packaging

Early innings of multi-year growth



Packaging revenue >\$800M in FY'21

#1 in bond pad, bump and TSV

Broad product portfolio + full-flow lab

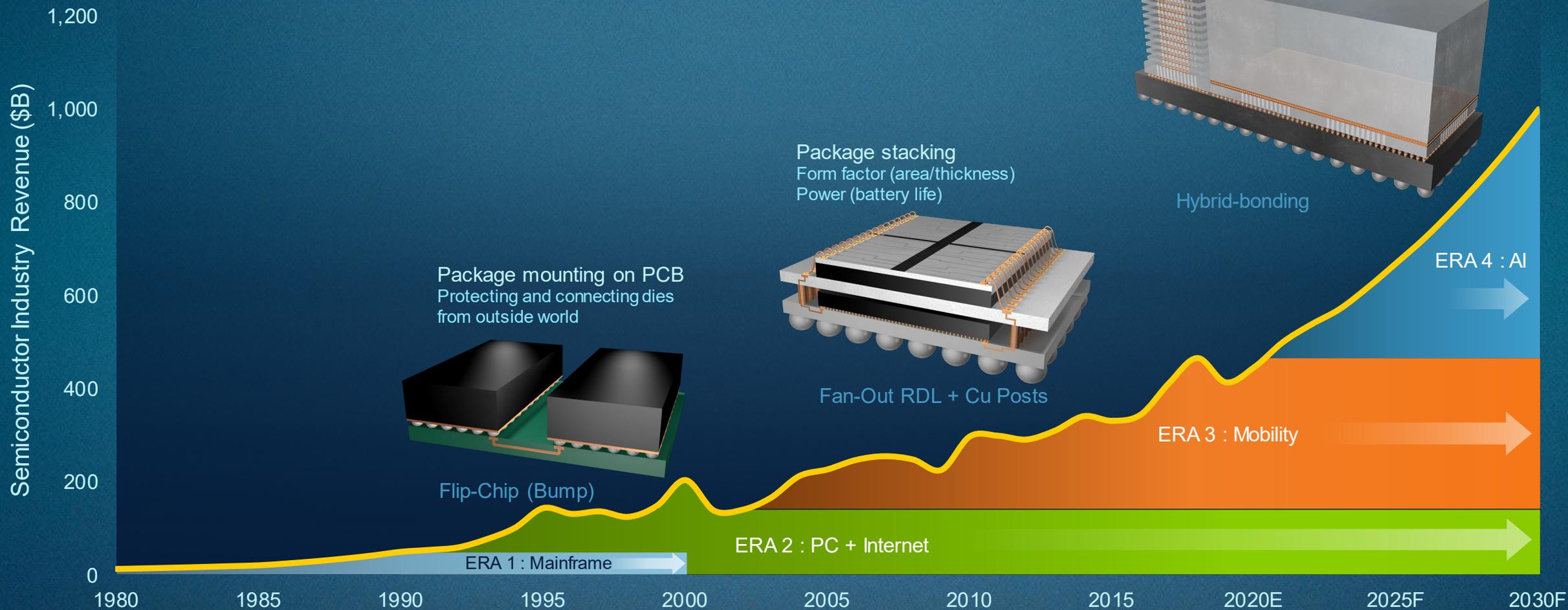
Key eco-system partnerships

Delivering system level PPACT gains
↓ R, ↓ power, ↓ area, ↑ performance

TSV = Through-Silicon Via

BIGGEST

Computing Wave Yet



Source: SEMI, VLSI, Applied Materials

Applied Materials External Use

TAKEAWAY

Messages

1. ICAPS markets fuel data generation at the edge and demand for leading-edge logic and memory in the cloud
2. Advanced packaging enables the PPACT™ benefits associated with Moore's Law to continue
3. Applied's unique portfolio breadth enables outperformance in ICAPS and advanced packaging

* Non-GAAP adjusted EPS

Applied Materials External Use

